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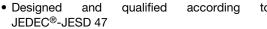
### Vishay Semiconductors

## Thyristor High Voltage, Phase Control SCR, 50 A



PRODUCT SUMMARY					
Package	TO-247L				
I <sub>T(AV)</sub>	50 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V				
V <sub>T</sub> (typ.)	1.1 V				
I <sub>GT</sub> (typ.)	40 mA				
T <sub>J</sub> max.	150 °C				
Diode variation	Single SCR				

#### **FEATURES**











FREE

#### **APPLICATIONS**

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

#### **DESCRIPTION**

The VS-50TPS12 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V <sub>RRM</sub> /V <sub>DRM</sub>		1200	V		
On-state voltage	V <sub>T</sub>	50 A, T <sub>J</sub> = 125 °C	1.1	V		
Average rectified forward current	I <sub>T(AV)</sub>		50			
Maximum continuous RMS on-state current	I <sub>RMS</sub>		79	Α		
Non-repetitive peak surge current	I <sub>TSM</sub>		630			
Maximum rate of rise	dV/dt		1000	V/µs		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +150	°C		

VOLTAGE RATINGS			
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA
VS-50TPS12L-M3	1200	1300	10



PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 112 °C, 180° conduction half sine wave		-	50	
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>			-	79	Α
Peak, one-cycle non-repetitive surge current	I	10 ms sine pulse, rated $V_{\mbox{\scriptsize RRM}}$ applied		-	530	
reak, one-cycle non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	Initial $T_J = T_J$	-	630	
12t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	maximum	-	1405	A <sup>2</sup> s
I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, no voltage reapplied		-	1986	
I <sup>2</sup> √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, T <sub>J</sub> = 125 °C		-	19 850	A²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>			-	0.83	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	T. <sub>I</sub> = 125 °C			0.95	V
Low level value of on-state slope resistance	r <sub>t1</sub>	- IJ= 125 C		-	0.58	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>			-	0.51	
On state valtage	V <sub>T</sub>	50 A, T <sub>J</sub> = 25 °C		1.2	1.32	V
On-state voltage		100 A, T <sub>J</sub> = 25 °C		1.4	1.6	v
Rate of rise of turned-on current	dl/dt	T <sub>J</sub> = 25 °C		-	150	A/µs
Holding current	I <sub>H</sub>	I <sub>H</sub>		-	300	
Latching current	Anode supply = 6 V, resistive load, $T_J = 25 ^{\circ}\text{C}$		25 -0	-	350	A
December and discretization of the contract	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 25 °C		-	0.05	mA
Reverse and direct leakage current		T <sub>J</sub> = 125 °C		-	10	
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ , $R_q$ - $k = \infty \Omega$		-	1000	V/µs

TRIGGERING							
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS	
Peak gate power	P <sub>GM</sub>	10 ma aina nula	o no voltage reapplied	-	10	W	
Average gate power	P <sub>G(AV)</sub>	10 ms sine puis	e, no voltage reapplied	-	2.5	VV	
Peak gate current	I <sub>GM</sub>			-	2.5	Α	
Peak negative gate voltage	-V <sub>GM</sub>			-	10		
	V <sub>GT</sub>	T <sub>J</sub> = -40 °C	Anode supply = 6 V resistive load	-	1.6	V	
Required DC gate voltage to trigger		T <sub>J</sub> = 25 °C		-	1.5	\ \ \	
		T <sub>J</sub> = 150 °C		-	1		
		T <sub>J</sub> = -40 °C		-	160		
Required DC gate to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	45	100	mA	
		T <sub>J</sub> = 150 °C		-	60		
DC gate voltage not to trigger	$V_{GD}$	T 150 °C V reted value			0.2	٧	
DC gate current not to trigger	$I_{\mathrm{GD}}$	T <sub>J</sub> = 150 °C, V <sub>DRM</sub> = rated value			3	mA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Turn-on time	t <sub>gt</sub>	$I_T = 50 \text{ A}, V_D = 50 \% V_{DRM}, I_{gt} = 300 \text{ mA}, T_J = 25 ^{\circ}\text{C}$	1.5	-	
Turn-off time	t <sub>q</sub>	$I_{T} = 50 \text{ A, V}_{D} = 80 \% \text{ V}_{DRM}, \text{ dV/dt} = 20 \text{ V/}\mu\text{s, t}_{p} = 200 \mu\text{s}$ $I_{gt} = 100 \text{ mA, dI/dt} = 10 \text{ A/}\mu\text{s, V}_{R} = 100 \text{ V, T}_{J} = 150 \text{ °C}$	92	ı	μs



THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40	150	°C	
Maximum thermal resistance, junction to case		$R_{thJC}$		-	0.35		
Maximum thermal resistance, junction to ambient		$R_{thJA}$		-	40	°C/W	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.2	-		
Mounting torque minimum maximum				6	(5)	kgf · cm	
				12	(10)	(lbf · in)	
Marking device			Case style Super TO-247L		50TPS12I		

△R <sub>thJ-HS</sub> CONDUCTION PER JUNCTION											
DEVICE	S	SINE HALF-WAVE CONDUCTION RECTANGULAR WAVE CONDUCTION						UNITS			
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-50TPS12L-M3	0.143	0.166	0.208	0.299	0.490	0.099	0.168	0.223	0.311	0.494	°C/W

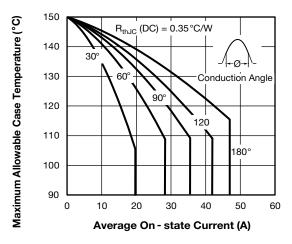


Fig. 1 - Current Rating Characteristics

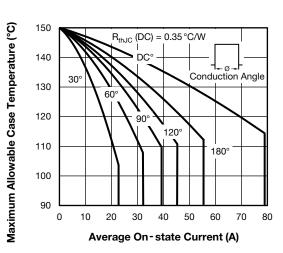


Fig. 2 - Current Rating Characteristics

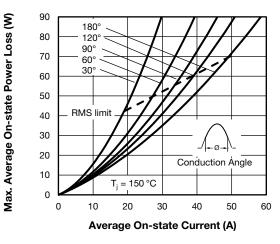


Fig. 3 - On-State Power Loss Characteristics

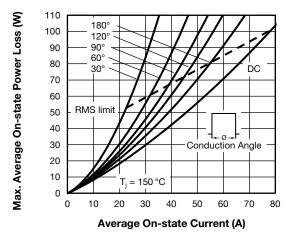


Fig. 4 - On-State Power Loss Characteristics

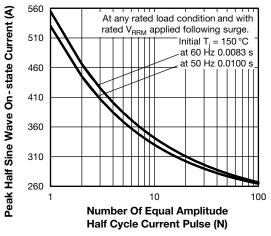


Fig. 5 - Maximum Non-Repetitive Surge Current

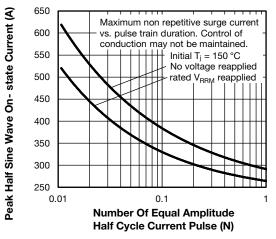


Fig. 6 - Maximum Non-Repetitive Surge Current

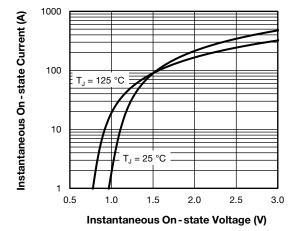


Fig. 7 - On-State Voltage Drop Characteristics

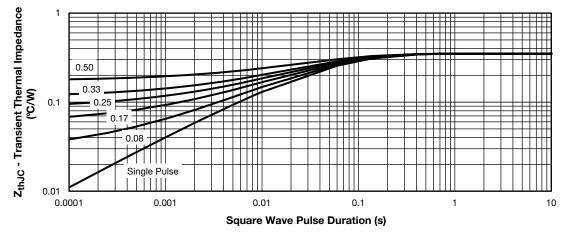
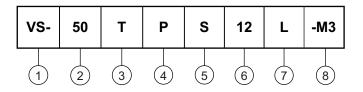


Fig. 8 - Gate Characteristics



#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current code (50 = 50 A)

Circuit configuration:

T = thyristor

4 - P = TO-247 package

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage code (12 = 1200 V)

7 - Package L = long lead

- M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (example)							
PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-50TPS12L-M3	25	contact factory	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95626</u>					
Part marking information	www.vishay.com/doc?95007				



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